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(54) **ACOUSTIC WAVE DEVICE AND
MANUFACTURING METHOD THEREOF**

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ABSTRACT

An acoustic wave device includes: a substrate; a first electrode on the substrate; a piezoelectric layer on the first electrode; and a second electrode on the piezoelectric layer. A bonding interface is located between the substrate and the first electrode. The full width at half maximum (FWHM) in the X-ray diffraction pattern of the crystal plane <002> of the piezoelectric layer is between 10 arc-sec and 3600 arc-sec.

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